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100% Probe Tested to These Parameters @ 25°C

Guaranteed tested on (sample basis)

COMPLEMENTARY SWITCHING DIODES (*AVAILABLE IN 16 PIN DIP ARRAYS)

Part Number	V _{BR} Volts Min. @ I _R =100µA	I _R µA Max. @ V _R Volts		I _F mA Min. @ V _F =1.0V	C _T pf Max. @ 0V	t _{rr} Max. in N-Sec @ I _F =10mA; recover to I _R =-1 mA	GEOM-ENTRY
		5.0 @ 75V	0.025 @ 20V				
1N914* EQUIVALENT TO IN4148	100	5.0 @ 75V	0.025 @ 20V	10	4.0	4.0	Q
1N914-N	100	1.0 @ 75V	0.001 @ 20V	10	4.0	100	Q
1N914-R*	60	5.0 @ 50V	0.025 @ 20V	10	6.0	50	R
1N914-RN	60	1.0 @ 50V	0.001 @ 20V	10	6.0	500	R
1N914-HV	200	1.0 @ 75V	0.001 @ 20V	10	4.0	100	Q
1N914-B	75	5.0 @ 60V	0.25 @ 20V	50	4.0	4.0	Q
DE100 DF100	75	I _R µA Max @ V _R = 60V		200	2	6.0	S T

HIGH POWER SWITCHING DIODES

Part Number	V _{BR} Volts Min. I _R = 100µA	I _R µA Max. @ V _R Volts	V _F Max. @ I _F Amps	C _T pf Max. @ 0V	t _{rr} Max. I _F = 1 Amp I _R = -.1 Amp	GEOM-ENTRY
DE 3101/5	100	10µA at 90V	1µA at 80V	300 pf	35 ns	U
DE 3101/2	100	10µA at 90V	1µA at 80V	200 pf	35 ns	V

DIODE QUADS

Part Number	ΔV _F mV Max. @ I _F =-1.0mA	Matched Characteristic		I _F mA Min. @ V _F =1.0V	C _T pf Max.	t _{rr} Max @ I _F =10mA; recover to I _R =-1 mA	GEOM-ENTRY
		V _{BR} Volts Min. @ I _R =100µA	I _R µA Max. @ V _R Volts				
DI 914-1Q -2Q -3Q	10	75	.025 @ 65 .025 @ 50 .025 @ 35	10	3.0	*750 nsec.	W
DI 914-1QM -2QM -3QM	3.5	75	.010 @ 65 .010 @ 50 .020 @ 35	20	3.0	*750 nsec.	W

DIODE QUAD BRIDGES

Part Number	V _{BR} (Each Diode) Volts Min. @ I _R =100µA	I _R (Each Diode) µA Max. @ V _R Volts	I _F (Each Diode) mA Min. @ V _F =1.0V	C _T (Each Diode) pf Max.	t _{rr} Max. (Each Diode) @ I _F =10mA; recover to I _R =-1mA	GEOM-ENTRY
DI 914-1B -2B -3B	75 60 45	.010 @ 65 .010 @ 50 .010 @ 35	20	3.0	*750 nsec.	X

*Also available with t_{rr} Max. @ 10 nsec.

*Also available with t_{rr} Max. @ 10 nsec.

